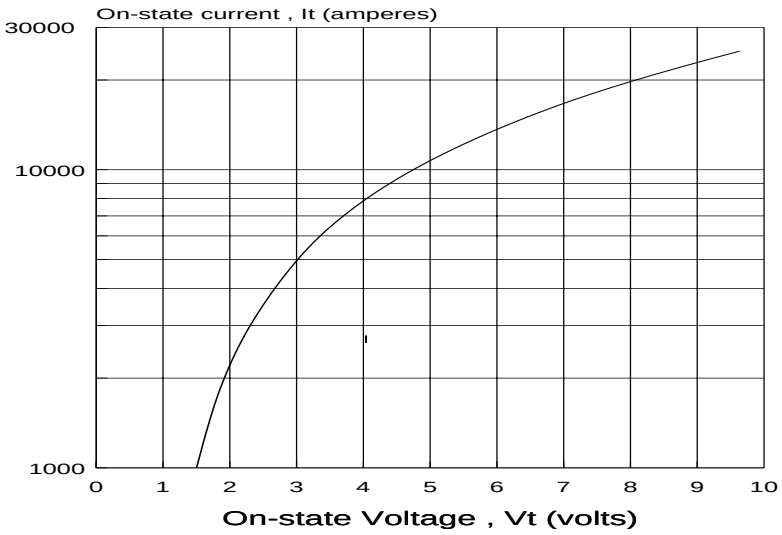
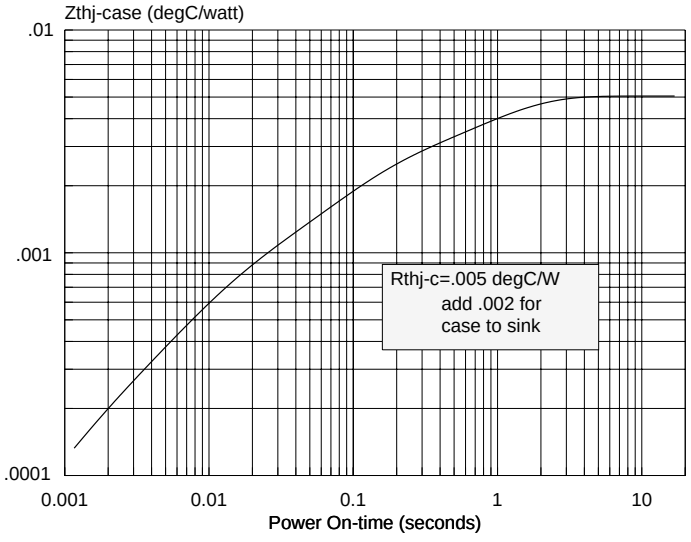
C792
100mm THYRISTOR PRESSPAK
6000V / 2100A

Type C792 thyristor is suitable for phase control applications such as for HVDC valves,static VAR compensators and synchronous motor drives. The silicon junction design utilizes a second generation pilot gate and a unique orientation of emitter shorts which promote the lateral expansion of conducting plasma resulting in lower spreading losses while achieving high dv/dt withstand. It is supplied in an industry accepted disc-type package,ready to mount using commercially available heat dissipators and mechanical clamping hardware.

MAXIMUM ON-STATE CHARACTERISTIC
Initial TJ=105 degC / 8ms pulse





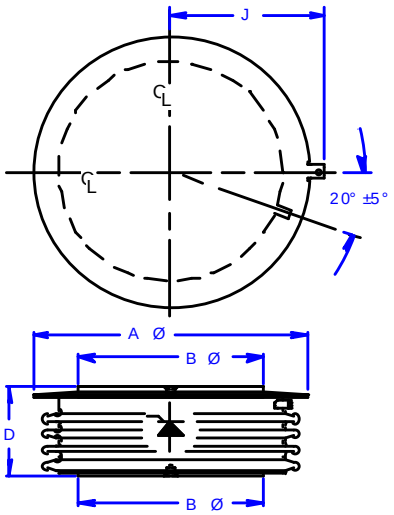
o1a:t305tau

REPETITIVE PEAK REVERSE AND OFF-STATE BLOCKING VOLTAGE

T_J = 0 to 115°C

MODEL	V_{DRM} (volts)	V_{RRM} (volts)
C792FP	6000	6000
C792ET	5900	5900
C792EN	5800	5800
C792ES	5700	5700
C792EM	5600	5600
C792EE	5500	5500

MECHANICAL OUTLINE



AF = 5.65 in (143.5 mm)
BF=3.92 in (99.4 mm)
D=1.45 in (36.8 mm)

ELECTRICAL CREEPAGE / STRIKE

1.6 / 1.0 in
40.6 / 25.4 mm

CLAMPING FORCE (range)

17000-19000 lb.

175 GREAT VALLEY PKWY. MALVERN, PA 19355
USA

11/13/01

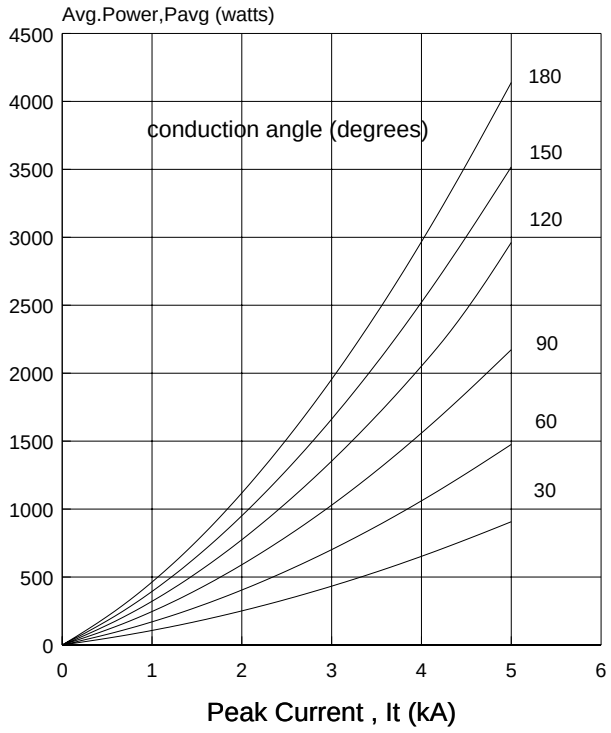
LIMITING CHARACTERISTICS AND RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAXIMUM VALUES	UNIT S
Repetitive peak off-state and reverse voltage	V_{DRM} V_{RRM}	T_j=0 to +115°C	see table	V
Repetitive working crest voltage	V_{DWM} V_{DRM}	T_j=0 to 115°C	.8V_{DRM} .8V_{RRM}	V
Rep.off-state and reverse leakage current	I_{DWM} I_{RRM}	V_{DWM} V_{RWM} T_j=115°C	150 150	ma ma
On-state Voltage	V_{TM}	I_T=2000A t_p=8.3ms T_j=115°C	1.90	V
Critical DC gate current/voltage to trigger on	I_{GT} V_{GT}	V_D=12VDC T_j=25°C	150 3	ma V
Non-trigger gate current/voltage	I_{GD} V_{GD}	V_D=.8V_{DRM} T_J=115°C	8 —	ma V
Critical rate of rise of off-state	dv/dt	0.67V_{DRM} T_j=115C	2000	V/us
Critical rate of of on-state	di/dt_{rep}	0.67 V_{DRM} see req'd gating	100	A/us
Peak recovery current	$I_{RM(rec)}$	di/dt=2A/us T_j=115°C	118	A
Peak half-cycle non-repetitive surge current	I_{TSM}	t_p=8.3ms t_p=10 ms	35 34	kA
Circuit commutated turn-off time	t_q	di/dt=5A/us dv/dt=20V/us	600	us

GATE CIRCUIT REQUIREMENTS

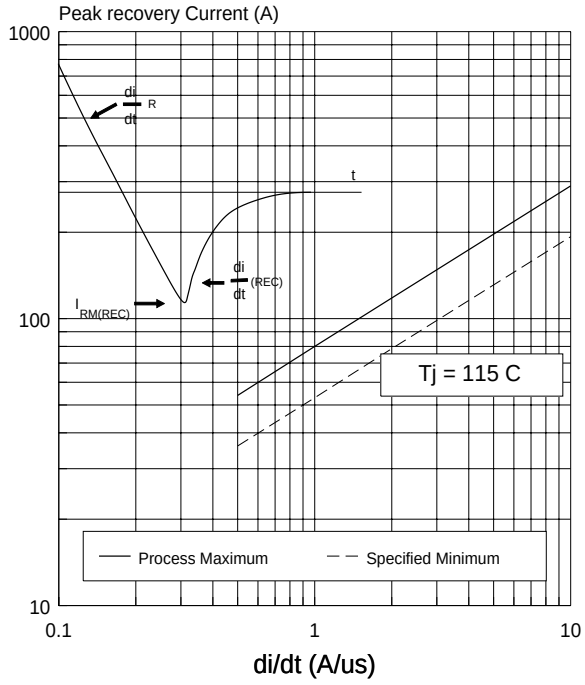
Open circuit voltage	40 - 50 V
Short circuit current	3 A minimum
Current risetime	0.5 us nominal
Pulse duration	10-20 us

FULL CYCLE AVERAGE POWER DISSIPATION
Sine Wave-includes spread loss

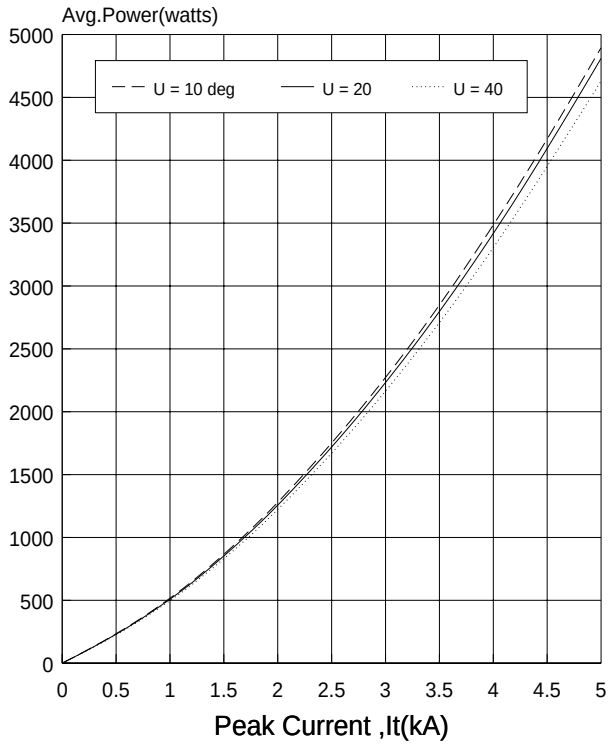


6RT300

PEAK RECOVERY CURRENT
versus
COMMUTATING di/dt

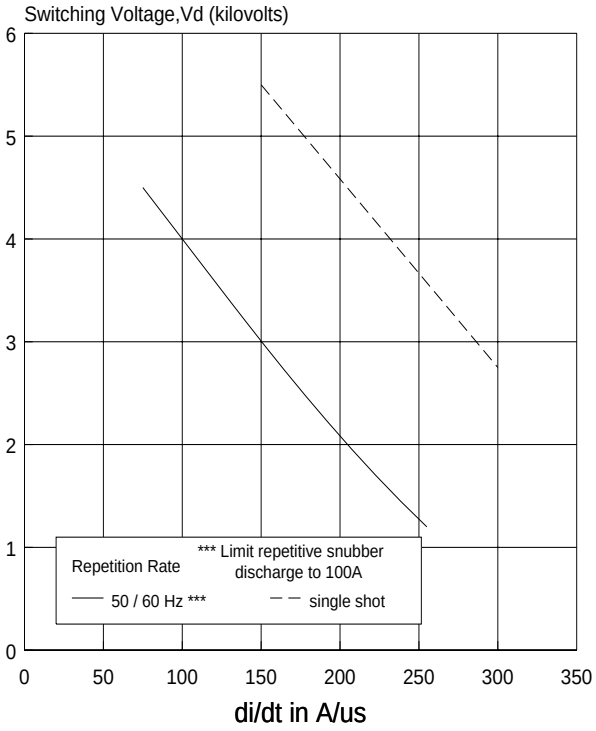


FULL CYCLE AVERAGE POWER DISSIPATION
120-Deg Conduction-includes spread loss
as a function of overlap angle ,U



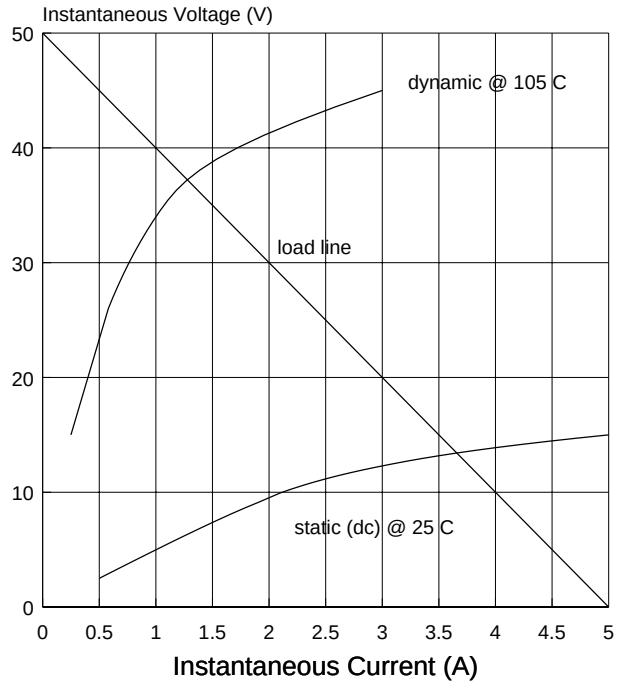
6RT300

INRUSH CURRENT (di/dt) RATING
versus
SWITCHING VOLTAGE



T300

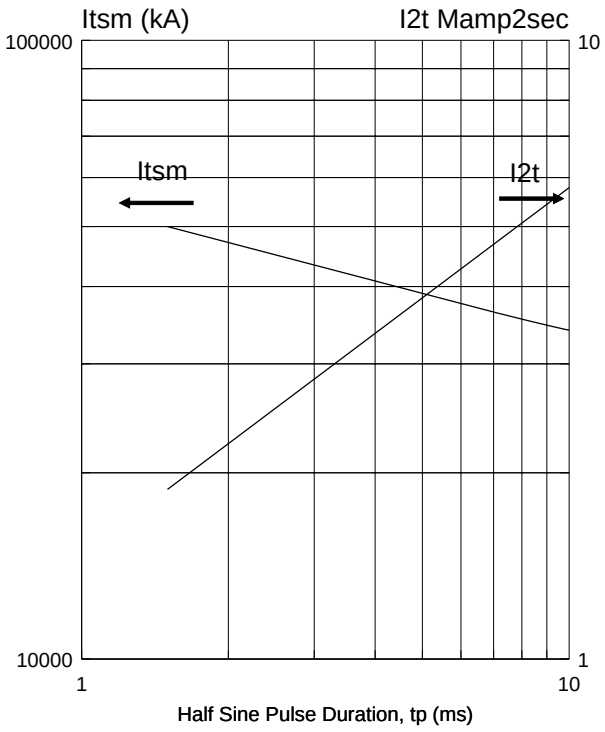
Gate Characteristics and Gate Supply Requirements



T302

- THYRISTOR GATE IMPEDANCE
  Enhanced by fast rising gate voltage,increasing anode bias and junction temperature.It is at a minimum for dc current, zero anode bias and low temperature.
- GATE SUPPLY
  Prefer 50V/10 ohm for supporting the di/dt rating and life expectancy. The short circuit current risetime should be nominally 0.5us and the duration longer than the expected delay time for all magnitudes of anode bias. Practically 10-30us is recommended followed by a back porch of 750ma if needed to sustain conduction.
- MINIMUM ACCEPTABLE GATE CURRENT
  The intersection of the load line and gate impedance characteristic indicates the minimum value of actual current needed during the delay time interval to support di/dt.A different load line meeting this criterion may be used.
- MAXIMUM GATE RATINGS
  Peak gate power,Pgm(100us) = 300 W
  Average gate power,Pg(av) = 50W
  Peak gate current,Igfm = 25 A
  Peak reverse voltage,Vgrm = 25 V

Non-Repetitive Surge Current and I2t for Fusing



01I:C792ITSM